

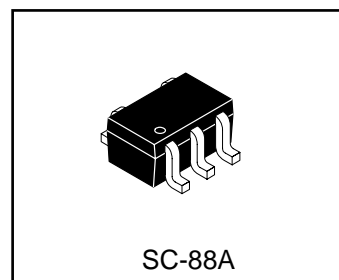
Dual NPN Digital Transistor

- Pb-Free Package is Available.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LUMG2NT1G
S-LUMG2NT1G

Ordering Information

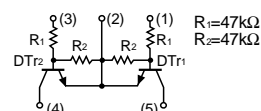
Device	Marking	Shipping
LUMG2NT1G S-LUMG2NT1G	G2	3000/Tape&Reel
LUMG2NT3G S-LUMG2NT3G	G2	10000/Tape&Reel



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Supply voltage	V _{CC}	50	Vdc
Input voltage	V _{IN}	-10 to +40	Vdc
Output current	I _O	30	mAdc
Output current	I _{C(Max.)}	100	mAdc
Power dissipation	P _D	150	mW *
Junction temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

* 120mW per element must not be exceeded.



●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I(off)}	-	-	0.5	V	V _{CC} =5V, I _O =100μA
Input voltage	V _{I(on)}	3	-	-	V	V _O = 0.3V, I _O =2mA
Output voltage	V _{O(on)}	-	0.1	0.3	V	I _O =10 mA, I _I =0.5mA
Input current	I _I	-	-	0.18	mA	V _I =5V
Output current	I _{O(off)}	-	-	0.5	μA	V _{CC} =50V, V _I =0V
DC current gain	G _I	68	-	-	V	V _O = 5V, I _O =5mA
Resistance ratio	R ₂ /R ₁	0.8	1	1.2	-	-
Transition frequency	f _T	-	250	-	MHz	V _{CE} =10V, I _E = -5mA, f=100MHz *
Input resistance	R _I	32.9	47	61.1	kΩ	-

* Transition frequency of the device

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●Electrical characteristic curves

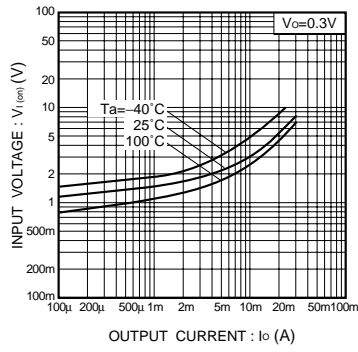


Fig.1 Input voltage vs. output current (on-characteristics)

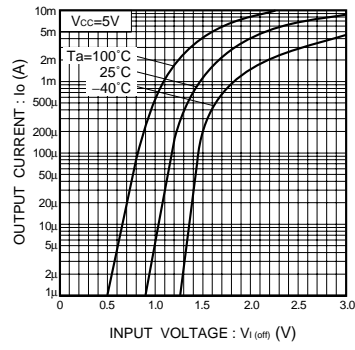


Fig.2 Output current vs. input voltage (off-characteristics)

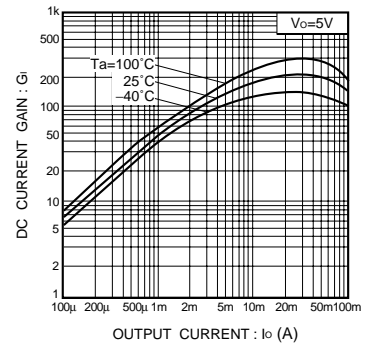


Fig.3 DC current gain vs. output current

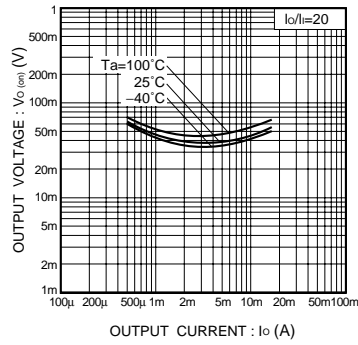
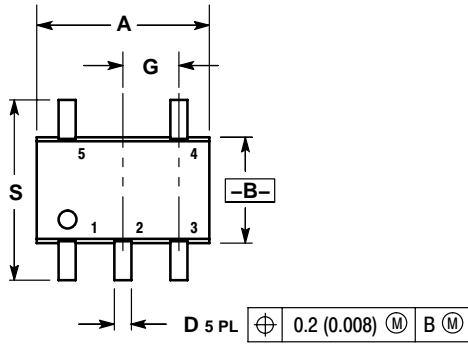


Fig.4 Output voltage vs. output current

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SC-88A



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

